

Semiconductor industry is in the era of engineered materials

- Engineered substrates continue to take a larger share of semiconductor content in fast growing markets
- European collaboration from substrate to system is a must to enable a significant role in these strategic markets.
- Timing is critical to maintain WW competitiveness
- Value demonstration from R&D to pilot production will ensure sustainable European leadership in Electronics and Optoelectronics.



Soitec – Who we are

DESIGNER & MANUFACTURER OF INNOVATIVE SEMICONDUCTOR MATERIALS

We design and deliver innovative substrates & solutions to enable our customers' products shaping everyday life

1

Leader Leader

2

Unique technologiesSMART CUTTM, SMART STACKING

4

High-growth marketsSMARTPHONES, AUTOMOTIVE, CLOUD & INFRASTRUCTURE, IOT

6

Wafer fabs (150, 200 & 300 mm) FRANCE, BELGIUM, SINGAPORE, CHINA*

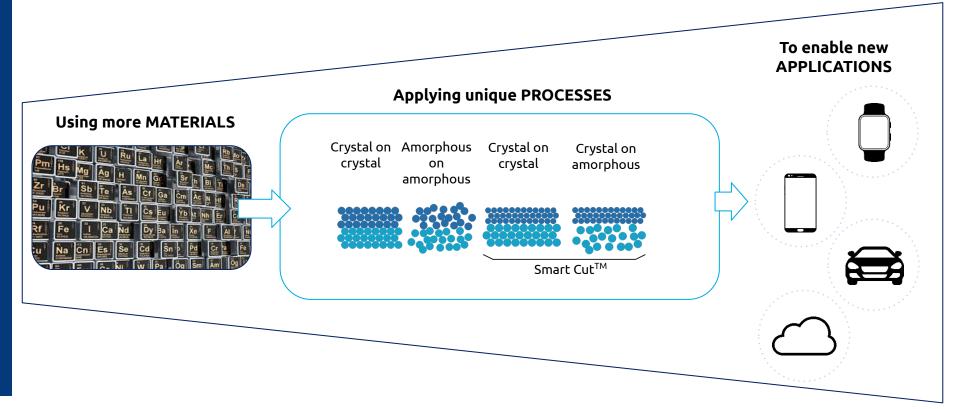
1,750

Employees Worldwide
GLOBAL PRESENCE**

*Partnership with Shanghai Simgui Technology Co. Ltd. (Simgui)
**December 2020



Engineered substrates allow us to push boundaries

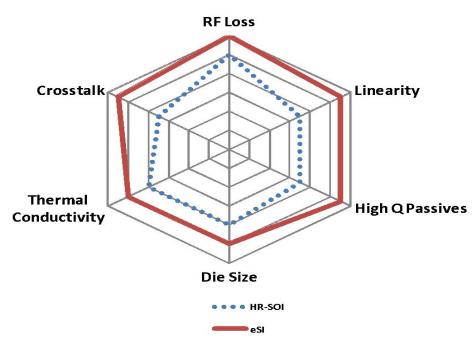


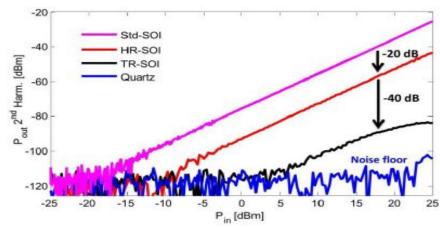
2 RFSOI: 1st
demonstration that
foundations are
making a difference



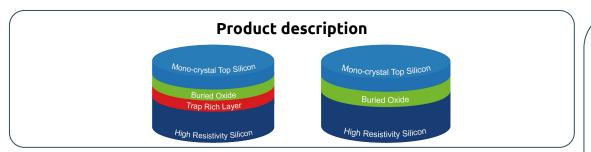
Substrate's direct impact on die performance

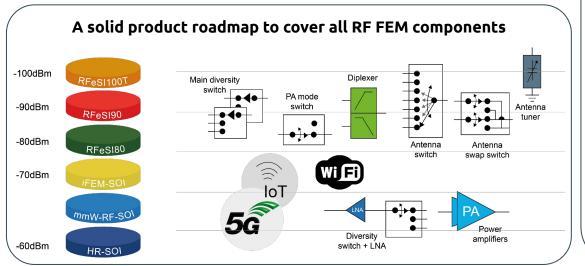
eSI vs. HR-SOI performance





RF-SOI: an industry standard for Front-End Module (FEM)

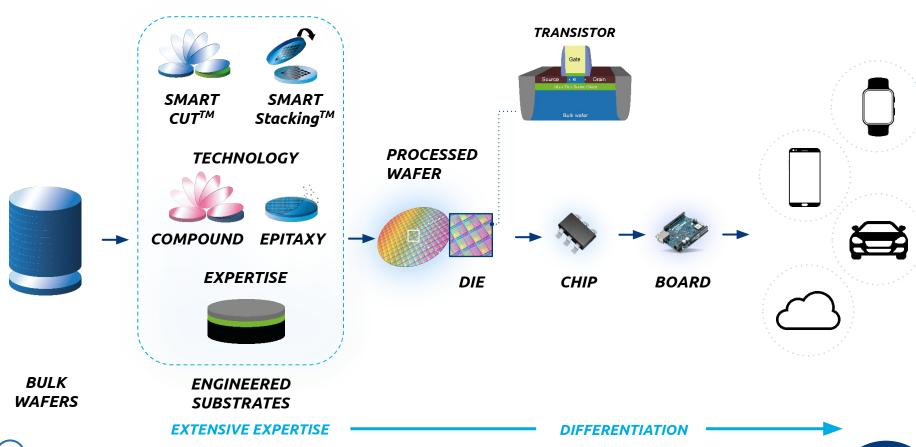




Value proposition

- RF-SOI is present in 100% of smartphones
- RF-SOI is a standard for RF FEM components (antenna tuners, switches, LNAs, PAs)
- RF-SOI is a unique platform for FEM integration
- RF-SOI provides inherent isolation and signal integrity for LTE and 5G
- Best in class performance per cost

A Collaboration across the whole value chain for system benefit





May. 21

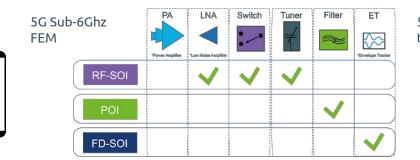


A broad product portfolio of engineered substrates to address 5G

RF **PROCESSOR &** PIEZO-ON-GaN FRONT-END CONNECTIVITY **INSULATOR MODULE** SOC POI GaN FD-SOI For high RF-SOI For radio frequency For power efficient, high performance For highly efficient (RF) 5G and power reliable integration of 5G filters mobile communication systems digital, analog and RF Mono-crystal Piezo Lay SiC or Si High Resistivity Silicol High Resistivity Silicon **SOI** products Piezo & compound products

A comprehensive 5G handset and base station offer for sub-6GHz and mmW

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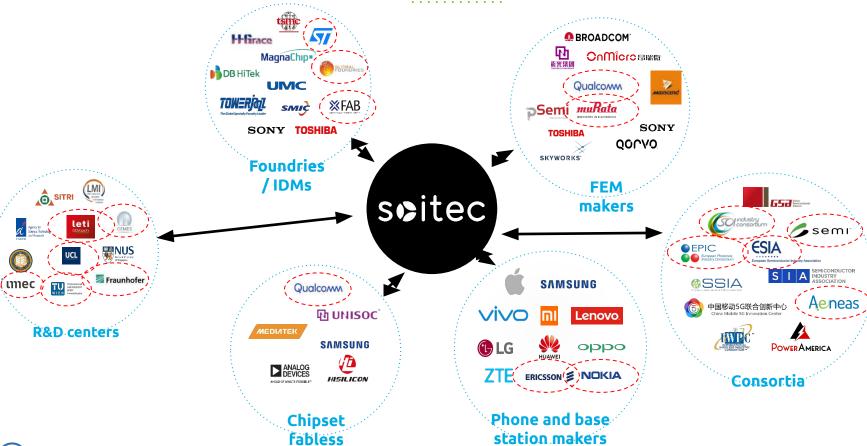


✓ Suitable solution

(*): No public data available for GaN



5G Differentiation requires wide collaboration - Europe has a play!



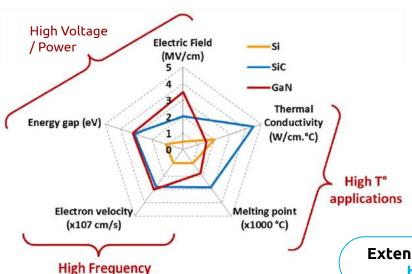


Automotive: Power Devices



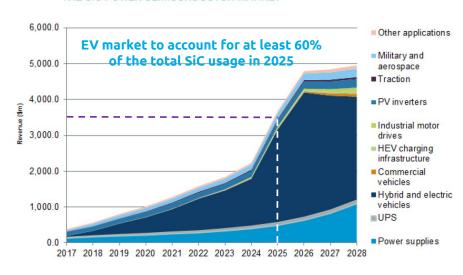
SiC: Key material to replace silicon in power application

Best in class material for high voltage, high temperature and high switching frequency operation



SiC power device forecast

THE SIC POWER SEMICONDUCTOR MARKET



Extensive usage of large-area SiC MOSFET devices ⇒ need for high production yield and high performance devices

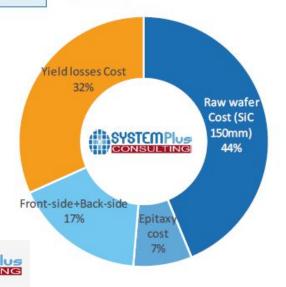
switching

SiC power devices Rapidly-growing market, driven by automotive EV

Example of SiC MOSFET Wafer FE Cost Breakdown

SiC wafer price is the major cost-driver within SiC FE manufacturing cost

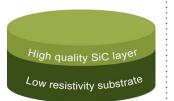
- Raw wafer Cost (SiC 150mm)
- Epitaxy cost
- Front-side+Back-side
- Yield losses Cost



Benefits of Smart Cut™ SiC substrate

System level

- Longer distance range
- Faster battery charging
- More reliable operation
- Smaller system footprint



Device and manufacturing level

- Target 40-70% less energy losses *vs* bulk SiC
- Target 15-30% higher manufacturing yield
- Target 5-10% smaller die size
- Simpler and cheaper manufacturing process

Supply chain

- Increased availability of ultra-prime substrates
- Independent, pure-play substrate supplier
- Fastest path to 200 mm transition



Smart Cut[™] solution: SiC Engineered Substrate

Current industry solution (monocrystalline bulk)

Device

Epi Layer (drift)

Conversion Buffer

Substrate

Smart CutTM's engineered epi-ready substrate solution

High quality SiC layer

Low resistivity substrate

Ultra-prime top crystal + very-low resistivity base wafer



Simpler process + Higher yield + Lower losses = lower \$ / device



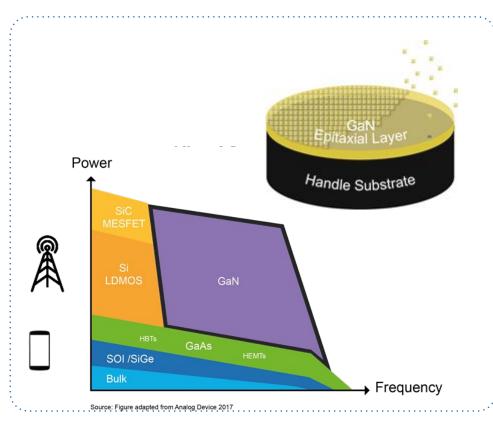
SiC from Substrate to Car, a full chain in Europe

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GaN epi wafers: leading technology for 5G - Opportunity for Power



Opportunities

- GaN on Silicon opens opportunity for integration
 - Power regulation
 - GaN on SOI is a possible integration path, requires multi-players collaboration

Future opportunities on power automotive & sensors









CONCLUSION



Semiconductor industry is in the era of engineered materials

- Engineered substrates continue to take a larger share of semiconductor content in fast growing markets: smartphones, automobile, cloud & infrastructure, IoT
- European collaboration from substrate to system is a must to enable a significant role in these strategic markets.
 - 5G: Multiple opportunities with major integration challenges and opportunities.
 - Automotive (Power Electronics): Major SiC & GaN based system leadership opportunity.
 - IOT & Edge AI: Best PPAC solutions can be enabled
 - Vcsel: Large diameter, long wavelength are strategic advantages we can bring.
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